

Abstract of the Disclosure

The present invention relates to a method for fabricating a semiconductor device with realizable advanced
5 fine patterns. The method includes the steps of: forming a hard mask insulation layer on an etch target layer; forming a hard mask sacrificial layer on the hard mask insulation layer; coating a photoresist on the hard mask insulation layer; performing selectively a photo-exposure process and
10 a developing process to form a photoresist pattern having a first width for forming a line pattern; etching selectively the hard mask sacrificial layer by using the photoresist pattern as an etch mask to form a sacrificial hard mask having a second width; removing the photoresist pattern;
15 etching the hard mask insulation layer by controlling excessive etching conditions with use of the sacrificial hard mask as an etch mask to form a hard mask having a third width; and etching the etch target layer by using the sacrificial hard mask and the hard mask as an etch mask to
20 form the line pattern having a fourth width, wherein the first width is wider than the fourth width.